

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

C. Amendments to the Claims.

## 1. (Currently Amended): A method, comprising:

cleaning a plasma reactor chamber part of a material redistributed  
thereon by a reactive plasma process, by placing the chamber part in a  
redistributed material solvent for at least 6 hours;

cleaning the chamber part with a plasma that includes oxygen as a  
source gas; and

ultrasonically cleaning the chamber part; wherein

the material includes photoresist polymers and the solvent  
includes acetone.

## 2. (Cancelled) The method of claim 1, wherein:

the material includes photoresist polymers and the solvent includes  
acetone.

## 3. (Original) The method of claim 1, wherein:

the chamber part comprises quartz.

## 4. (Cancelled): The method of claim 1, wherein:

the chamber part is placed in the solvent for at least 6 hours.

## 5. (Cancelled) The method of claim 1, further including:

cleaning the chamber part with a plasma that includes oxygen as a source  
gas.

## 6. (Previously Presented) The method of claim 1, wherein:

the plasma is formed with a radio frequency (RF) power in the general  
range of 500 to 1000 W.

## 7. (Previously Presented) The method of claim 1, further including:

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

rinsing the chamber part after cleaning with the solvent but before the plasma cleaning.

8. (Cancelled) The method of claim 5, further including:

5                   ultrasonically cleaning the chamber part.

9. (Previously Presented) The method of claim 1, further including:

                  baking the chamber part at a temperature in the general range of 75-150 °C.

10

10. (Currently Amended) A method of cleaning a plasma reactor chamber part, comprising:

                  plasma cleaning a chamber part of a material redistributed on the chamber part by a reactive plasma process, with a plasma having an etch selectivity between the chamber part and the redistributed material that is greater than 1:100; and

15

                  cleaning the chamber part with an organic solvent of the redistributed material by placing the chamber part in the organic solvent of the redistributed material prior to the plasma cleaning.

11. (Original) The method of claim 10, wherein:

20                   the chamber part comprises quartz and the plasma includes oxygen as a source gas.

12. (Original) The method of claim 10, wherein:

                  the plasma is formed with a radio frequency (RF) power in the general range of 500 to 1000 W.

25

13. (Original) The method of claim 10, wherein:

                  the redistributed material includes photoresist polymers.

30   14. (Cancelled) The method of claim 10, further including:

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

cleaning the chamber part with a solvent of the redistributed material.

15. (Currently Amended) A method of cleaning reactive plasma chamber parts, comprising the steps of:

- 5           applying an organic solvent to a surface of a chamber part;  
            oxygen plasma cleaning the chamber part; ~~and~~  
            ultrasonically cleaning the chamber part after the oxygen plasma  
            cleaning; and  
            rinsing the chamber part with a liquid that evaporates at a lower  
            temperature than water after the ultrasonic cleaning.

16. (Original) The method of claim 15, wherein:  
            the organic solvent includes acetone.

10   17. (Cancelled) The method of claim 15, further including:  
            rinsing the chamber part with de-ionized water after applying the  
            organic solvent.

15   18. (Cancelled) The method of claim 15, further including:  
            ultrasonically cleaning the chamber part after the oxygen plasma cleaning.

19. (Cancelled) The method of claim 15, further including:  
            rinsing the chamber part with a liquid that evaporates at a lower  
            temperature than water after the ultrasonic cleaning.

20   20. (Original) The method of claim 15, further including:  
            baking the chamber part at a temperature greater than 80 °C for at least 15  
            minutes.

25